

Applicant : Shunpei YAMAZAKI et al.  
Serial No. : 09/769,765  
Filed : January 26, 2001  
Page : 8

Attorney's Docket No.: 12732-008001 / US4579

REMARKS

Claims 17-24 and 48-75 are pending in this application, with claims 17, 48, 55, 62 and 69 being independent. Claims 1-16 and 25-47 have been cancelled, claims 17-19 and 21 have been amended, and claims 48-75 have been added.

Applicant hereby elects the invention of Group I, Species 3 (claims 17-24), which are directed to a semiconductor device having a first and second electrode on the first insulating film. Newly added claims 48-75 are also directed to such a device.

A check in the amount of \$400.00 is enclosed for a two-month extension of time. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: December 13, 2002

  
\_\_\_\_\_  
John F. Hayden  
Reg. No. 37,640

Fish & Richardson P.C.  
1425 K Street, N.W.  
11th Floor  
Washington, DC 20005-3500  
Telephone: (202) 783-5070  
Facsimile: (202) 783-2331

**Version with markings to show changes made**

**In the claims:**

**Claims 17-19 and 21 have been amended as follows:**

17. (Amended) A semiconductor device comprising:  
a first semiconductor layer and a second semiconductor layer on an insulating surface;  
a first insulating film on the first semiconductor layer and on the second semiconductor  
layer;  
a first electrode on the first insulating film, overlapping the first semiconductor layer;  
a second electrode on the first insulating film, overlapping the second semiconductor  
layer;  
a source wiring on the first insulating film;  
a second insulating film covering the first electrode and the source wiring;  
a gate wiring on the second insulating film, connected to the first electrode;  
a connection electrode on the second insulating film, connected to the source wiring and  
the first semiconductor layer; and  
a pixel electrode on the second insulating film, connected to the first semiconductor  
layer;  
wherein at least one end of the pixel electrode overlays the source wiring with the second  
insulating film interposed therebetween.

18. (Amended) A device according to claim 17, wherein the first electrode **[overlapping  
the first semiconductor layer]** is a gate electrode.

19. (Amended) A device according to claim 17, wherein a storage capacitor is formed by  
the second semiconductor layer **[connected to the pixel electrode, and]**, the second electrode  
**[connected to a gate wiring of an adjacent pixel, with]**, and the first insulating film **[as a  
dielectric]**.

21. (Amended) A device according to claim 17, wherein the gate wiring **[is formed from  
a film having]** comprising an element selected from the group consisting of[:]  
polysilicon doped with an impurity element which imparts one conductivity[:],  
W[:], WSix[:], Al[:], Cu[:], Ta[:], Cr[:], and Mo as its main constituent, and a lamination film of the elements.